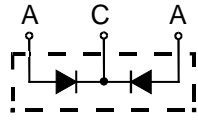
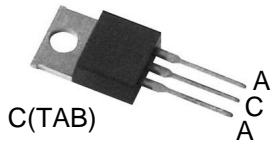


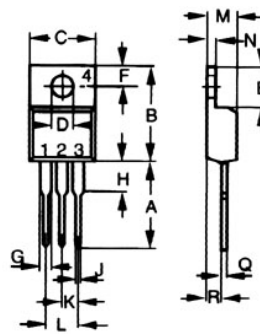
SBL2050CT thru SBL2060CT

Low V_F Schottky Barrier Rectifiers



A=Anode, C=Cathode, TAB=Cathode

Dimensions TO-220AB



Dim.	Inches		Millimeter	
	Min.	Max.	Min.	Max.
A	0.500	0.550	12.70	13.97
B	0.580	0.630	14.73	16.00
C	0.390	0.420	9.91	10.66
D	0.139	0.161	3.54	4.08
E	0.230	0.270	5.85	6.85
F	0.100	0.125	2.54	3.18
G	0.045	0.065	1.15	1.65
H	0.110	0.230	2.79	5.84
J	0.025	0.040	0.64	1.01
K	0.100	BSC	2.54	BSC
M	0.170	0.190	4.32	4.82
N	0.045	0.055	1.14	1.39
Q	0.014	0.022	0.35	0.56
R	0.090	0.110	2.29	2.79

	V_{RRM}	V_{RMS}	V_{DC}
	V	V	V
SBL2050CT	50	35	50
SBL2060CT	60	42	60

Symbol	Characteristics	Maximum Ratings	Unit
$I_{(AV)}$	Maximum Average Forward Rectified Current @ $T_c=95^\circ\text{C}$	20	A
I_{FSM}	Peak Forward Surge Current 8.3ms Single Half-Sine-Wave Superimposed On Rated Load (JEDEC METHOD)	250	A
V_F	Maximum Forward Voltage At 10.0A DC (Note 1)	0.75	V
I_R	Maximum DC Reverse Current @ $T_J=25^\circ\text{C}$ At Rated DC Blocking Voltage @ $T_J=100^\circ\text{C}$	1 50	mA
C_J	Typical Junction Capacitance Per Element (Note 2)	600	pF
$R_{\theta JC}$	Typical Thermal Resistance (Note 3)	2.0	$^\circ\text{C}/\text{W}$
T_J	Operating Temperature Range	-55 to +125	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$

NOTES: 1. 300us Pulse Width, 2% Duty Cycle.
2. Measured At 1.0MHz And Applied Reverse Voltage Of 4.0V DC.
3. Thermal Resistance Junction To Case.

FEATURES

- * Metal of silicon rectifier, majority carrier conduction
- * Guard ring for transient protection
- * Low power loss, high efficiency
- * High current capability, low V_F
- * High surge capacity
- * For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications

MECHANICAL DATA

- * Case: TO-220AB molded plastic
- * Polarity: As marked on the body
- * Weight: 0.08 ounces, 2.24 grams
- * Mounting position: Any

SBL2050CT thru SBL2060CT

Low V_f Schottky Barrier Rectifiers

